



PSMC-03-287/51

March 19, 2004

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/758,317 01/15/04 |

Vincent S. Chang et al.

HIGH TEMPERATURE HYDROGEN ANNEALING  
OF A GATE INSULATOR LAYER TO INCREASE  
ETCHING SELECTIVITY BETWEEN CONDUCTIVE  
GATE STRUCTURE AND GATE INSULATOR  
LAYER

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on March 25, 2004.

Stephen B. Ackerman, Reg.# 37761

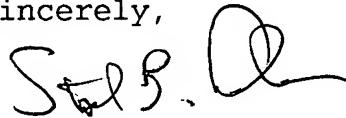
Signature/Date

Stephen B. Ackerman 3/25/04

U.S. Patent 6,335,278 to Miyazaki, "Method of Hydrogen Anneal to a Semiconductor Substrate," discloses a method of hydrogen annealing a semiconductor substrate for forming a semiconductor device such as a semiconductor integrated circuit in order to improve device performance and reliability.

U.S. Patent 6,569,741 to Houston et al., "Hydrogen Anneal before Gate Oxidation," discloses a process for preparing a silicon surface for gate dielectric formation.

Sincerely,

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman", with a large, stylized "A" at the end.

Stephen B. Ackerman,  
Reg. No. 37761

MAR 29 2004

Agreement Number

10/758,317

Vincent S. Chang et al.

01/15/04

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## FOREIGN PATENT DOCUMENTS

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.